

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
100V	26m $\Omega$ @10V	6A
	28m $\Omega$ @6V	
	31m $\Omega$ @4.5V	

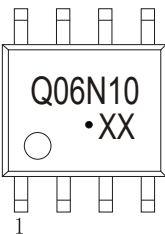
### Feature

- High density cell design for ultra low  $R_{DS(ON)}$
- Excellent package for good heat dissipation

### Application

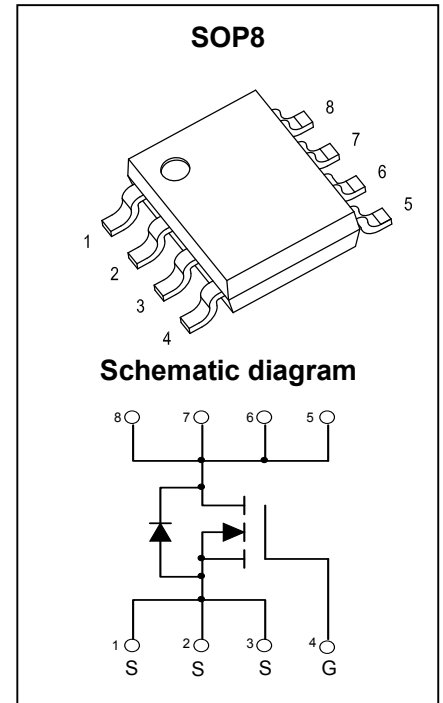
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

### MARKING:



Q06N10 = Device Code

XX = Date Code



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1,2</sup>	$I_D$	6	A
Pulsed Drain Current	$I_{DM}$	28	A
Single Pulsed Avalanche Current <sup>4</sup>	$I_{AS}$	35	A
Single Pulsed Avalanche Energy <sup>4</sup>	$E_{AS}$	306	mJ
Power Dissipation	$P_D$	1.7	W
Thermal Resistance from Junction to Ambient <sup>1,2</sup>	$R_{\theta JA}$	75	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

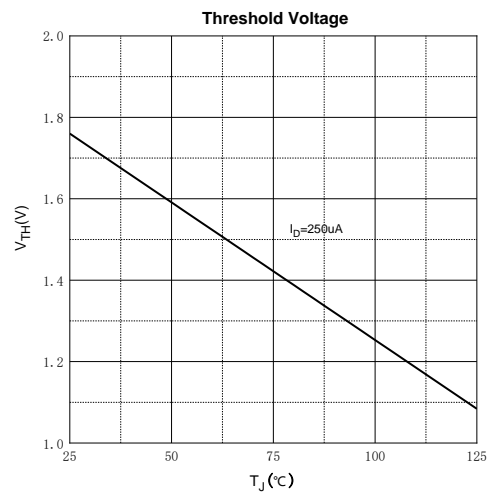
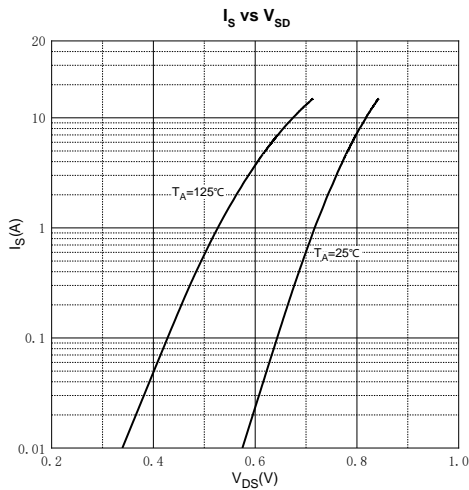
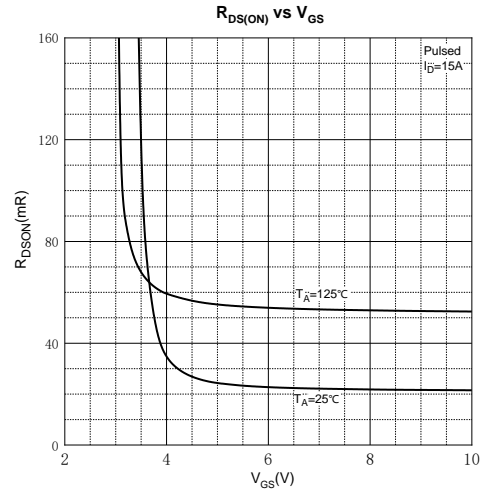
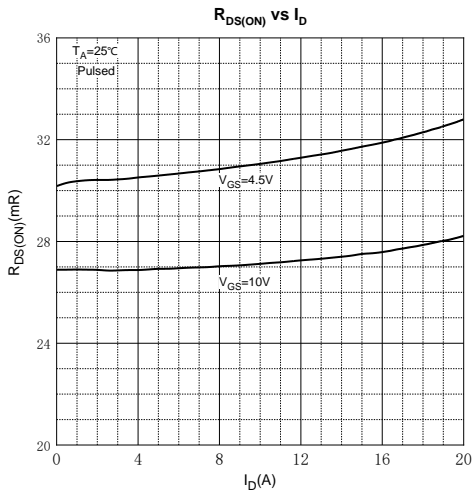
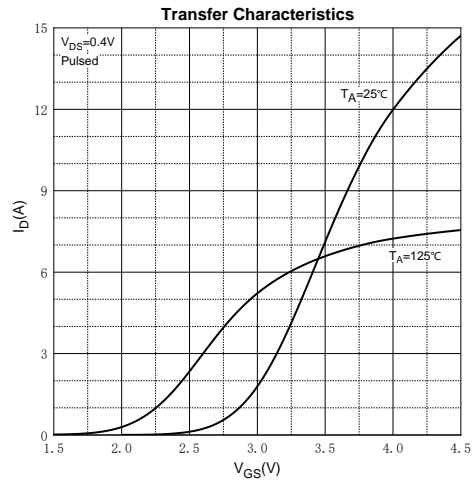
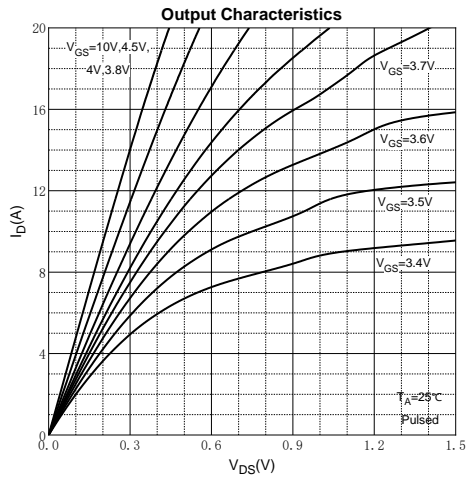
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.7	2.5	V
Drainsource onresistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 6A$		26	39	m $\Omega$
		$V_{GS} = 6V, I_D = 5A$		28	42	
		$V_{GS} = 4.5V, I_D = 4A$		31	46	
Forward transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 6A$		35		S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$		2249		pF
Output Capacitance	$C_{oss}$			87.7		
Reverse Transfer Capacitance	$C_{rss}$			82.8		
Gate resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.6		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 6A$		57.7		nC
GateSource Charge	$Q_{gs}$			16.7		
GateDrain Charge	$Q_{gd}$			6.0		
Turnon delay time	$t_{d(on)}$	$V_{DD} = 50V, R_G = 8.3\Omega, V_{GS} = 10V, R_L = 3\Omega$		7		ns
Turnon rise time	$t_r$			7		
Turnoff delay time	$t_{d(off)}$			28		
Turnoff fall time	$t_f$			7		
<b>Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 6A$			1.2	V

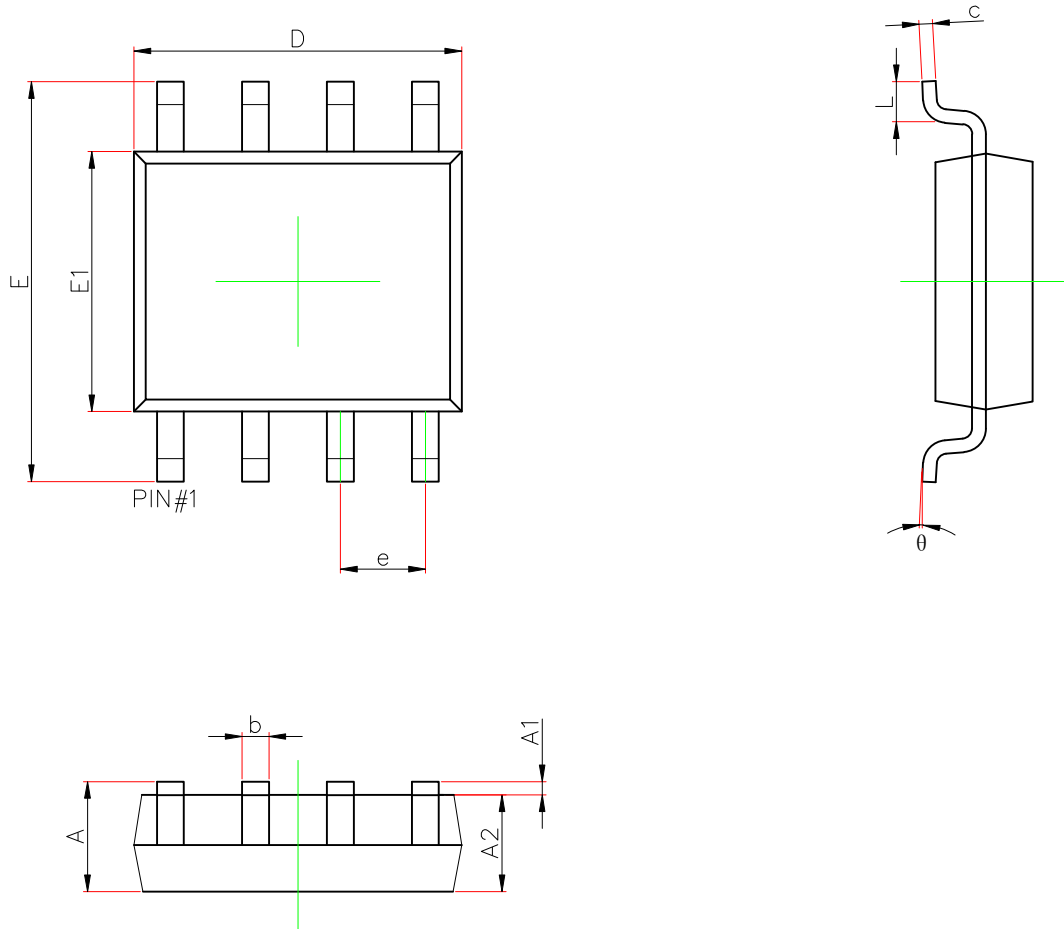
Notes :

1.  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR4 board with 1oz. single side copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .
2.  $R_{\theta JA}$  is measured in the steady state
3. Pulse test : Pulse width  $\leq 380\mu s$ , duty cycle  $\leq 2\%$ .
4.  $E_{AS}$  condition:  $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
$\theta$	0°	8°	0°	8°